

# EAST Search History (27 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	537	TEM and polysilicon and (grain adj boundary)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 10:22
L2	26	TEM near20 polysilicon near20 (grain adj boundary)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 10:43
L3	2	("5582640").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 11:29
L4	3	"6380560".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 11:55
L5	18	(("20010022364") or ("20040164300") or ("5922125") or ("6133075") or ("6168824") or ("6225645") or ("6479333") or ("6524896") or ("6730932") or ("6864127")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 11:56
L6	9	(US-20040164300-\$ or US-20010022364-\$).did. or (US-6864127-\$ or US-6730932-\$ or US-6524896-\$ or US-6479333-\$ or US-6225645-\$ or US-6133075-\$ or US-5922125-\$).did.	US-PGPUB; USPAT	OR	OFF	2007/10/25 12:55
L7	3	"6165824".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 12:56
L8	1	(US-6165824-\$).did.	USPAT	OR	OFF	2007/10/25 12:57
L9	11	(("5922125") or ("6730932") or ("6165824") or ("6133075")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 12:59

## EAST Search History

L10	11	9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 13:09
L11	2	CN-1877861\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 13:25
L12	3	("6730932").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 13:27
L13	2	jp-10209465\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:07
L14	2	jp-10301147\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:05
L15	2	jp-10223530\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:01
L16	2	jp-10301146\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:05
L17	0	jp-223530\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:07
L18	2	jp-10223530\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:08
L19	2	jp-10247735\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:09

## EAST Search History

L20	2	jp-09162416\$-\$did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:10
L21	12	13 14 15 16 17 18 19 20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:19
L22	3631	((257/64) or (257/66) or (257/71) or (345/92)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:20
L23	18	22 and (lattice near4 (tem hrtem high\$1resolution tem high\$1resolution adj transmission adj electron adj microscopy)) and gate and source and drain and semiconductor and (substrate near2 insulat\$3 soi) and grain adj boundary near20 continuous\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/25 14:23
L24	83	((ohtani near2 hisashi).in. (yamazaki near2 shunpei).in. semiconductor adj energy.as.) and (lattice near4 (tem hrtem high\$1resolution tem high\$1resolution adj transmission adj electron adj microscopy)) and gate and source and drain and semiconductor and (substrate near2 insulat\$3 soi) and grain adj boundary near20 continuous\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:25
L25	0	((ohtani near2 hisashi).in. (yamazaki near2 shunpei).in. semiconductor adj energy.as.) and (lattice near4 (tem hrtem high\$1resolution tem high\$1resolution adj transmission adj electron adj microscopy)).clm. and gate.clm. and source.clm. and drain.clm. and (semiconductor silicon).clm. and ((substrate near2 insulat\$3 soi).clm. and (grain adj boundary) near20 (smooth\$2 continuous\$2).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:27

## EAST Search History

L26	2	((ohtani near2 hisashi).in. (yamazaki near2 shunpei).in. semiconductor adj energy.as.) and (lattice) .clm. and gate.clm. and source.clm. and drain.clm. and (semiconductor silicon).clm. and ((substrate near2 insulat\$3) soi). clm. and (grain adj boundary) near20 (smooth\$2 continuous\$2). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 14:28
S1	318	dcfl direct adj coupled adj field adj effect adj transistor adj logic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 07:09
S2	318	dcfl direct adj coupled adj field adj effect adj transistor adj logic.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 19:55
S3	153	(dcfl direct adj coupled adj field adj effect adj transistor adj logic).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/14 19:55
S4	4	(EP-562719-\$).did. or (JP-01222484-\$).did. or (WO-200259972-\$ or EP-562719-\$). did.	EPO; JPO; DERWENT	OR	OFF	2004/05/15 12:49
S5	0	("jp-35786615\$-\$ did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/15 12:50
S6	0	jp-035786615\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/15 12:50
S7	0	jp-5786615\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/15 12:50
S8	5	"5786615"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 13:23

## EAST Search History

S9	2	("5786615").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 13:28
S10	0	wo-0259972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 13:29
S11	1	wo-200259972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:30
S12	4	"239534".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:16
S13	4451	imoto.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:16
S14	15	imoto.in. and gate adj (region layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:17
S15	1	wo-200259972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:31
S16	1	"200259972"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/16 14:39
S17	551	imoto.in. and @ad<"20012401"	EPO; DERWENT	OR	OFF	2004/05/16 14:41
S18	83	imoto.in. and @ad>"20012201"	EPO; DERWENT	OR	OFF	2004/05/16 14:41
S19	11	imoto.in. and @ad>"20012201" and semiconductor	EPO; DERWENT	OR	OFF	2004/05/16 14:41

## EAST Search History

S20	5	(WO-2059972-\$ or EP-562719-\$). did. or (JP-01222484-\$).did. or (EP-562719-\$ or WO-200259972-\$). did.	EPO; JPO; DERWENT	OR	OFF	2004/05/16 20:16
S21	83	(257/274).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/05/17 07:49
S22	2	((257/274).CCLS.) and back adj gate and (N-well P-well N adj well P adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/17 07:50
S23	8	(US-6307223-\$ or US-6281705-\$ or US-6107128-\$).did. or (EP-562719-\$ or WO-2059972-\$).did. or (JP-01222484-\$).did. or (WO-200259972-\$ or EP-562719-\$). did.	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/17 11:18
S24	8	(US-6107128-\$ or US-6281705-\$ or US-6307223-\$).did. or (EP-562719-\$ or WO-2059972-\$).did. or (JP-01222484-\$).did. or (EP-562719-\$ or WO-200259972-\$). did.	USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/17 09:49
S25	83	(257/274).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/05/17 19:15
S26	466	(257/371).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/05/17 19:15
S27	542	((257/274).CCLS.) ((257/371).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 20:15
S28	101	(((257/274).CCLS.) ((257/371).CCLS.)) and (gate adj (region layer) back adj gate back-gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/17 19:16
S29	17	(US-5963803-\$ or US-5973370-\$ or US-5990535-\$ or US-6023186-\$ or US-6031267-\$ or US-6040610-\$ or US-6207998-\$ or US-6281554-\$ or US-6281705-\$ or US-6307223-\$ or US-6320233-\$ or US-6509615-\$ or US-5763922-\$ or US-5900665-\$ or US-5950081-\$).did. or (US-20030205767-\$ or US-20030155619-\$).did.	US-PGPUB; USPAT	OR	OFF	2004/05/17 19:25

## EAST Search History

S30	3	((US-5963803-\$ or US-5973370-\$ or US-5990535-\$ or US-6023186-\$ or US-6031267-\$ or US-6040610-\$ or US-6207998-\$ or US-6281554-\$ or US-6281705-\$ or US-6307223-\$ or US-6320233-\$ or US-6509615-\$ or US-5763922-\$ or US-5900665-\$ or US-5950081-\$).did. or (US-20030205767-\$ or US-20030155619-\$).did.) and jfet	US-PGPUB; USPAT	OR	OFF	2004/05/17 19:25
S31	7749	source same drain same alternatively	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 11:24
S32	2865	source same drain same alternatively and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 11:24
S33	739	source same drain same alternatively same (connect connected connecting) and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 11:24
S34	151	source same drain same alternatively same (connect connected connecting) and cmos.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 11:27
S35	4	source near6 drain near6 alternatively near6 (connect connected connecting) and cmos.ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 13:01
S36	21	source near6 drain near6 alternatively near6 (connect connected connecting) and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 13:03
S37	2	("6281705").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 13:03

## EAST Search History

S38	23	(US-6509615-\$ or US-6320233-\$ or US-6281554-\$ or US-6207998-\$ or US-6040610-\$ or US-6031267-\$ or US-6023186-\$ or US-5763922-\$ or US-5973370-\$ or US-5950081-\$ or US-5963803-\$ or US-5990535-\$ or US-5900665-\$ or US-6307223-\$ or US-6281705-\$ or US-6107128-\$). did. or (US-20030155619-\$ or US-20030205767-\$).did. or (WO-2059972-\$ or EP-562719-\$). did. or (JP-01222484-\$).did. or (WO-200259972-\$ or EP-562719-\$). did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 16:59
S39	64	jfet.ti,ab,clm. and cmos.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 18:33
S40	2	jfet.ti,ab,clm. and cmos.ti,ab,clm. and (gaas gallium adj arsenide sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 18:43
S41	182	jfet and cmos and (gaas gallium adj arsenide sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 18:43
S42	35883	(cmos same gallium adj arsenide gaas).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 18:44
S43	120	(cmos same (gallium adj arsenide gaas)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 19:36
S44	3	steps near20 (body bias back-gate back adj gate) near20 (source drain) adj electrode near20 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/05/18 19:38
S45	36	(438/188).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 20:15
S46	1	((438/188).CCLS.) and gate adj contact near20 channel near20 electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 20:52

## EAST Search History

S47	4931	((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 20:53
S48	139	(((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371)).CCLS.) and gate adj contact and (jfet junction adj field adj effect adj transistor cmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 21:02
S49	1221	((438/188) or (438/223) or (438/224) or (438/225) or (438/226) or (438/227) or (438/228)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 21:02
S50	22	(((438/188) or (438/223) or (438/224) or (438/225) or (438/226) or (438/227) or (438/228)).CCLS.) and gate adj contact and (jfet junction adj field adj effect adj transistor cmos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/05/18 21:02
S59	4	"239534".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 10:58
S60	1	wo-200259972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 10:59
S61	0	wo-2002059972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 10:59
S62	1	wo-200259972\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 11:04
S63	2	@pd="20020801" and imoto.in.	EPO; DERWENT	OR	OFF	2005/05/28 11:08
S64	4	(("6281705") or ("6307223") or ("5600266") or ("4117587")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/29 07:36

## EAST Search History

S65	0	("enhancement near3(CMOS CMOSFET)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 13:57
S66	233	enhancement near3 (CMOS CMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 14:16
S67	4	enhancement near3 (CMOS CMOSFET) and JFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 14:00
S68	0	enhancement near3 (CMOS CMOSFET) and ("GaAs:Si" "GaAs:Ge")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 14:17
S69	0	enhancement near3 (CMOS CMOSFET) and ("GaAs:Si" "GaAs:Ge" Si adj doped near2 GaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 14:18
S70	0	enhancement near3 (CMOS CMOSFET) and ("GaAs:Si" "GaAs:Ge" Si adj doped near2 GaAs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:19
S71	67	("GaAs:Si" "GaAs:Ge" Si adj doped near2 GaAs) and (logic logical switch switches)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:20
S72	0	("GaAs:Si" "GaAs:Ge" Si adj doped near2 GaAs) and (logic logical switch switches) and NFET and PFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:20
S73	0	("GaAs:Si" "GaAs:Ge" Si adj doped near2 GaAs) and (logic logical switch switches) and NMOS and PMOS and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:24

## EAST Search History

S74	9747	("low" "lower" decrease decreased decreasing reduce reduced reducing) near3 power and (CMOS CMOSFET).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:26
S75	222	("low" "lower" decrease decreased decreasing reduce reduced reducing) near3 power and (CMOS CMOSFET).ti,ab,clm. and enhancement adj mode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 14:26
S76	32	("low" "lower" decrease decreased decreasing reduce reduced reducing) near3 power and (CMOS CMOSFET).ti,ab,clm. and enhancement adj mode and GaAs	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/28 15:01
S77	295	doping near3 channel near8 (MESFET JFET CMOS CMOSFET NMOSFET NMOS PMOS PMOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 15:08
S78	19	implant near3 channel near6 JFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/28 15:08
S79	2	"6307223".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 07:09
S80	3	JFET and (CMOS CMOSFET) and gate near4 ((same" opposite p-type n-type) adj conductivity) near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 07:40
S81	22	JFET and gate near4 ((same" opposite p-type n-type) adj conductivity) near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 10:01
S82	2468	(after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:02
S83	531	forming near10 (after, before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:03

## EAST Search History

S84	31	forming near10 ("P-well" "N-well" "well") near10 (after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:11
S85	5	forming near10 (wiring) near10 (after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:13
S86	0	forming near10 (back-gate) near10 (after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:13
S87	0	forming near10 (back-gate back adj gate) near10 (after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 10:14
S88	5	forming near10 (back-gate back adj gate contact adj region) near10 (after before) near10 (channel adj (layer region))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:08
S89	104	taddiken.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:08
S90	2	taddiken.in. and jfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:10
S91	2	taddiken.in. and bfl.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:26
S92	333832	jfet na dburied adj gate near4 conductivity adj type	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:26
S93	3	jfet and buried adj gate near6 (conductivity adj type)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:48

## EAST Search History

S94	1	parasitic adj bipolar and buried adj gate and jfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:52
S95	20	parasitic and buried adj gate and jfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:56
S96	0	insulated adj buried adj gate and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 11:57
S97	21	insulated near5 buried adj gate and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 12:02
S98	11	insulated near3 buried adj gate and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 12:04
S99	1	jfet near4 (combined combination) near4 trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 12:05
S100	0	jfet near4 (combined combination) near4 (vertical adj (MOS UMOS UMOSFET))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 12:06
S101	50	jfet and (cmos cmosfet) and trench near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/29 13:05
S102	5553	((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371) or (438/188) or (438/22\$1)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/05/29 13:06
S103	5	S102 and cmos and buried adj gate and parasitic and ("low" "lower" improved reduced reduction reducing decrease decreased decreasing) near4 power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 13:08

## EAST Search History

S10 4	5	S102 and cmos and buried adj gate and parasitic and ("low" "lower" improved reduced reduction reducing decrease decreased decreasing) near4 power and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 13:34
S10 5	2	"5117587".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 13:35
S10 6	4	"4117587".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 13:35
S10 7	5	"956774".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 17:07
S10 8	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2005/11/17 17:08
S10 9	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2005/11/17 17:08
S11 0	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 17:15
S11 1	0	("patidar.xp.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 14:48
S11 2	765	patidar.xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 14:48
S11 3	169	oen.xp. and weld\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 15:42
S11 4	7	oen.xp. and test\$3 near8 weld\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 15:43

## EAST Search History

S11 5	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2005/11/18 17:08
S11 6	0	(US-20050104132-\$).did. and "not" near4 "gate"	US-PGPUB	OR	OFF	2005/11/18 16:03
S11 7	0	"not" near4 "between " near4 drain near4 "gate"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:04
S11 8	0	"not" near8 "between " near8 drain near8 "gate" near8 source	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:05
S11 9	580629	complementary JFET junction adj field adj effect CMOS CMOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:06
S12 0	7352207	((complementary JFET) (junction adj field adj effect) CMOS CMOSFET) and "low" (reduced reduce reduction decrease decreasing decreases)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:09
S12 1	461486	((complementary JFET) (junction adj field adj effect) CMOS CMOSFET) and ("low" "lower" reduced reduce reduction decrease decreasing decreases)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:09
S12 2	0	((complementary JFET) (junction adj field adj effect) CMOS CMOSFET) and ("low" "lower" reduced reduce reduction decrease decreasing decreases) and gate near8 "not" near8 "between"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 16:09
S12 3	1	(US-20050104132-\$).did. and profile	US-PGPUB	OR	OFF	2005/11/18 17:08
S12 4	1	(US-20050104132-\$).did. and impurity near3 profile	US-PGPUB	OR	ON	2005/11/18 18:18

## EAST Search History

S12 5	6621	((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371) or (438/188) or (438/223) or (438/224) or (438/225) or (438/226) or (438/227) or (438/228)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/18 18:19
S12 6	9	S125 and ((complementary near1 (field adj effect) CMOS CMOSFET).ti,ab,clm. and (deplete\$3 near4 channel) and (reverse near3 bias\$3) and (reduce reduction reducing "lower" "low" decreas\$3) near3 power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/18 18:23
S12 7	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2006/04/27 10:42
S12 8	0	S127 and positive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/27 10:42
S12 9	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2006/07/22 22:03
S13 0	1	S129 and reverse\$2 adj bias\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/22 22:26
S13 1	1	S129 and impurity adj profile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/22 23:32
S13 2	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/23 08:33
S13 7	10590	depletion and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 09:09
S13 8	3271	depletion and (cmos cmosfet) and (n-well "n well" n-type adj "well")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 09:09

## EAST Search History

S14 0	28	deplet\$3 adj mode and (cmos cmosfet) and (n-well "n well" n-type adj "well") and ("full"\$1 complete\$2) near2 deplet\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 10:28
S14 1	17	deplet\$3 adj mode and (cmos cmosfet) and (n-well "n well" n-type adj "well") and ("full"\$1 complete\$2) near2 deplet\$3 and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 10:33
S14 2	17	deplet\$3 adj mode and (cmos cmosfet) and (n-well "n well" n-type adj "well") and ((full"\$1 complete\$2) near2 deplet\$3) and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 10:45
S14 3	4	deplet\$3 adj mode and (cmos cmosfet) and (fully adj depleted adj channel) and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 11:00
S14 4	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2006/07/23 10:48
S14 5	1	S144 and (enhancement deplet\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/23 10:48
S14 6	7	deplet\$3 adj mode and (cmos cmosfet nmosfet nmos) and (fully adj depleted adj channel) and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 11:01
S14 7	7	deplet\$3 adj mode and (cmos cmosfet pmosfet pmos) and (fully adj depleted adj channel) and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 11:41
S14 8	1	enhancement adj mode and JFET and (fully adj depleted adj channel) and @ad<"20020124"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:36
S14 9	6704	((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371) or (438/188) or (438/223) or (438/224) or (257/225) or (257/226) or (257/227) or (257/228)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/23 13:50

## EAST Search History

S15 0	289	S149 and (junction adj field adj effect jfet mosfet misfet mesfet).ti, ab,clm. and gate near10 source near10 drain near10 (outside between)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:40
S15 1	289	S149 and (junction adj field adj effect jfet mosfet misfet mesfet).ti, ab,clm. and gate near10 source near10 drain near10 (outside between) and @ad<"200201017"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/23 12:40
S15 7	1	WO-200259972\$-\$ DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 13:16
S15 8	2	jp-61267358\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 13:17
S15 9	1	jp-57086615\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 13:18
S16 0	8	(("6307223") or ("6281705") or ("4117587")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 14:51
S16 1	0	jp-05786615\$-\$ did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 14:55
S16 2	62	(saito near1 yutaka).in. and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/21 15:00
S16 3	2	("5786615").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 15:10
S16 4	2	S163 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 17:10

## EAST Search History

S16 5	0	"6307223".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 17:10
S16 6	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/21 17:10
S16 7	0	("gatenear4"not"near4"between"nea r4drain").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 10:24
S16 8	0	gate near4 "not" near4 "between" near4 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:25
S16 9	0	gate near8 "not" near8 "between" near8 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:25
S17 0	25061	gate near8 side near8 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:28
S17 1	16276	gate near8 side near8 drain and (JFET MOSFET MOS field adj effect adj (device transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:29
S17 2	2627	gate near8 side near8 drain and (JFET MOSFET MOS field adj effect adj (device transistor)) and second adj3 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:30
S17 3	5	gate near8 side near8 drain and (JFET MOSFET MOS field\$1effect adj (device transistor)) and second adj3 transistor and (direct adj coupling adj field\$1effect dcfl)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:36
S17 4	4	non\$1central adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:37

## EAST Search History

S17 5	0	non\$1central near2 gate and (transistor field adj effect MOS MOSFET JFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:38
S17 6	5653	(peripheral non\$1central) near4 gate and (transistor field adj effect MOS MOSFET JFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 10:39
S17 7	203	(peripheral non\$1central) near4 gate and (transistor field adj effect MOS MOSFET JFET) and S172	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:11
S17 8	3390	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:16
S17 9	1245	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm. and gate near10 drain.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:17
S18 0	1094	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm. and (gate near10 source near10 drain).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:18
S18 1	901	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm. and (gate near6 source near6 drain).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:22
S18 2	158	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm. and (gate near6 source near6 drain).ti,ab,clm. and gate near4 (location located locate position positioning positioned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:50
S18 3	106	(junction adj field adj effect adj (transistor device) jfet).ti,ab,clm. and (gate near6 source near6 drain).ti,ab,clm. and gate near4 (location located locate position positioning positioned) and @ad<"20020131"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:50

## EAST Search History

S18 4	6	lateral adj (jfet junction adj field adj effect adj transistor) near8 (vertical adj (jfet junction adj field adj effect adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 18:17
S18 5	0	"6307223".pn. and compound	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 10:47
S18 6	2	"20050104132".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 10:48
S18 7	2	"20050104132".pn. and (gate gate adj region gate adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 10:51
S18 8	176	jfet and bottom adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 11:23
S18 9	99	jfet and bottom adj gate	USPAT	OR	ON	2007/03/23 11:24
S19 0	26	jfet and bottom adj gate adj region	USPAT	OR	ON	2007/03/23 11:25
S19 1	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2007/03/23 11:41
S19 2	1	(US-20050104132-\$).did. and gate adj region	US-PGPUB	OR	ON	2007/03/23 12:00
S19 3	1	(US-20050104132-\$).did. and gate adj wire	US-PGPUB	OR	ON	2007/03/23 12:09
S19 4	7222	((257/256) or (257/272) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371) or (438/188) or (438/223) or (438/224) or (438/225) or (438/226) or (438/227) or (438/228)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/23 12:10
S19 5	0	(jfet junction adj field adj effect) and gate near8 ("not" near4 "between")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 12:11

## EAST Search History

S19 6	37	(jfet junction adj field adj effect) and gate near8 (dcfl direct adj coupl\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 12:15
S19 7	2	(imoto.in. sony.as.) and (jfet junction adj field adj effect).clm. and gate near8 (dcfl direct adj coupl\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 12:16
S19 8	23	(imoto.in. sony.as.) and (jfet junction adj field adj effect).clm. and gate near8 ("between")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 12:17
S19 9	10	(imoto.in. sony.as.) and (jfet junction adj field adj effect).clm. and gate near8 ("between").clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 12:17
S20 0	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/13 18:14
S20 1	2	("4638344").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/13 18:15
S20 2	2	("5929503").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 11:01
S20 3	2	("5892264").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 11:29
S20 4	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 11:36
S20 5	2	("4638344").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 11:36

## EAST Search History

S20 6	20	("4638344").URPN.	USPAT	OR	OFF	2007/08/14 11:50
S20 7	5	S206 and (cmos cmosfet)	USPAT	OR	ON	2007/08/14 11:37
S20 8	266	asymmetric near3 gate and transistor	USPAT	OR	OFF	2007/08/14 11:50
S20 9	165	asymmetric near3 gate and (cmos cmosfet) and transistor	USPAT	OR	OFF	2007/08/14 11:50
S21 0	69	asymmetric near1 gate and (cmos cmosfet) and transistor	USPAT	OR	OFF	2007/08/14 12:06
S21 1	2923	(asymmetry asymmetric separat\$3) near1 gate and (cmos cmosfet) and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 12:07
S21 2	270	(asymmetry asymmetric separat\$3) near1 gate near1 channel and (cmos cmosfet) and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 12:27
S21 3	161	gate adj contact adj region and (cmos cmosfet)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 12:28
S21 4	146	gate adj contact and (cmos cmosfet) and jfet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 12:29
S21 5	0	("s000135").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 14:58
S21 6	2	("6307223").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 15:05

## EAST Search History

S21 7	2	("4373253").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 15:07
S21 8	8	igfet and jfet and (cmos cmosfet) and common adj drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 15:11
S21 9	2	(igfet mos mosfet) near20 jfet near20 (cmos cmosfet) and common adj (drain source)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 15:27
S22 0	31	(igfet mos mosfet) near20 jfet near20 (cmos cmosfet) and (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 15:27
S22 1	1	("5670393").URPN.	USPAT	OR	OFF	2007/08/14 16:26
S22 2	8	(inverter invertor) near20 (cmos cmosfet) near20 jfet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 16:27
S22 3	15	(inverter invertor) near20 (mos mosfet igfet cmos cmosfet) near20 jfet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 16:27
S22 4	18	(inverter invertor) near20 (mos mosfet igfet cmos cmosfet) near20 jfet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 16:28
S22 5	12	(inverter invertor) near20 (mos mosfet igfet cmos cmosfet) near20 jfet and @ad<"20010124"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 16:29

## EAST Search History

S22 6	12	(inverter invertor) near20 (mos mosfet igfet cmos cmosfet) near20 jfet and @ad<"20010124" and jfet and (mos mosfet igfet cmos cmosfet)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 16:48
S22 7	65	jfet near6 (replace replaced replacing) near6 (mos igfet nmos nmosfet mosfet)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 16:51
S22 8	27	jfet near6 (replace replaced replacing) near6 (mos igfet nmos nmosfet mosfet) and @ad<"20010124"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 16:51
S22 9	7	jfet near6 (replace replaced replacing) near6 (mos igfet nmos nmosfet mosfet) and @ad<"20010124" and (inverter invertor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 17:50
S23 0	50	"low" adj noise near6 (silicon adj carbide gallium adj nitride compound adj semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 17:59
S23 1	1	"5517152".pn. and noise	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:01
S23 2	2	"5517152".pn. and speed	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:18

## EAST Search History

S23 3	7645	((257/256) or (257/272) or (257/273) or (257/274) or (257/368) or (257/369) or (257/370) or (257/371) or (438/188) or (438/223) or (438/224) or (438/225) or (438/226) or (438/227) or (438/228)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/14 18:19
S23 4	51	S233 and (cmos cmosfet inverter invertor) and jfet and gate adj (contact region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:21
S23 5	63	S233 and (cmos cmosfet inverter invertor) and (jfet junction adj field adj effect adj transistor) and gate adj (contact region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:26
S23 6	12	(sony.as. (tsutomo near1 imoto).in.) and (cmos cmosfet inverter invertor field adj effect adj transistor).clm. and (jfet junction adj field adj effect adj transistor).clm. and gate adj (contact region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:30
S23 7	0	(sony.as. (tsutomo near1 imoto).in.) and (cmos cmosfet inverter invertor field adj effect adj transistor).clm. and (jfet junction adj field adj effect adj transistor).clm. and gate near1 (contact near1 region).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/14 18:30
S23 8	1	(US-20050104132-\$).did.	US-PGPUB	OR	OFF	2007/10/25 08:30
S23 9	1	(US-20050104132-\$).did. and gate near4 contact	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 08:31
S24 0	1	(US-20050104132-\$).did. and (gate near4 contact (contact near2 region))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 08:36

## EAST Search History

S24 1	2	"4373253".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/25 10:21
----------	---	---------------	--	----	----	------------------